



DC COMPONENTS CO., LTD.
DISCRETE SEMICONDUCTORS

DMBT2369

TECHNICAL SPECIFICATIONS OF NPN EPITAXIAL PLANAR TRANSISTOR

Description

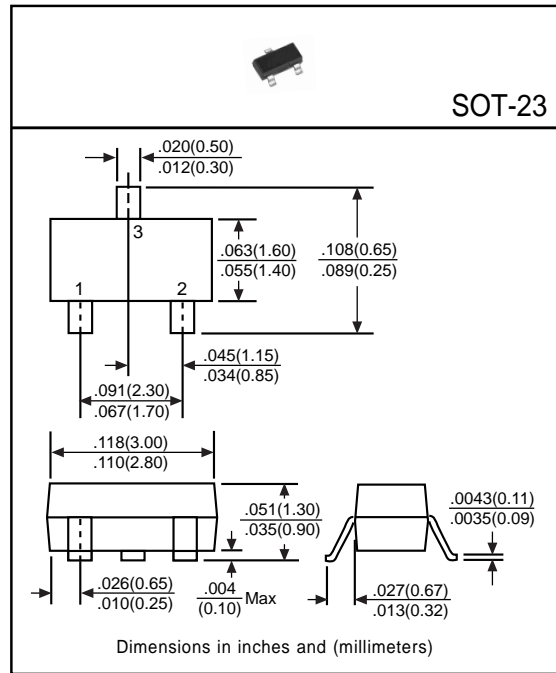
Designed for high speed switching applications.

Pinning

- 1 = Base
- 2 = Emitter
- 3 = Collector

Absolute Maximum Ratings (TA=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	40	V
Collector-Emitter Voltage	V _{CES}	40	V
Emitter-Base Voltage	V _{EBO}	4.5	V
Collector Current	I _C	500	mA
Total Power Dissipation	P _D	225	mW
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-55 to +150	°C



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CB0}	40	-	-	V	I _C =10μA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CES}	40	-	-	V	I _C =10μA, I _B =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	15	-	-	V	I _C =10mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	4.5	-	-	V	I _E =10μA, I _C =0
Collector Cutoff Current	I _{CBO}	-	-	400	nA	V _{CB} =20V, I _E =0
Collector-Emitter Saturation Voltage ⁽¹⁾	V _{CE(sat)}	-	-	250	mV	I _C =10mA, I _B =1mA
Base-Emitter Saturation Voltage ⁽¹⁾	V _{BE(sat)}	700	-	850	mV	I _C =10mA, I _B =1mA
DC Current Gain ⁽¹⁾	h _{FE1}	40	-	120	-	I _C =10mA, V _{CE} =1V
	h _{FE2}	20	-	-	-	I _C =100mA, V _{CE} =2V
Output Capacitance	C _{ob}	-	-	4	pF	V _{CB} =5V, f=1MHz, I _E =0

(1) Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%